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TDA2030

14W Hi-Fi AUDIO AMPLIFIER

DESCRIPTION

The TDA2030 is a monolithic integrated circuit in Pentawatt® package, intended for use as a low frequency class AB amplifier. Typically it provides 14W output power (d = 0.5%) at $14V/4\Omega$; at $\pm 14V$ or 28V, the guaranteed output power is 12W on a 4Ω load and 8W on a 8Ω (DIN45500).

The TDA2030 provides high output current and has very low harmonic and cross-over distortion.

Further the device incorporates an original (and patented) short circuit protection system comprising an arrangement for automatically limiting the dissipated power so as to keep the working point of the output transistors within their safe operating area. A conventional thermal shut-down system is also included.



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|-----------------------------------|-----------------------------------------------|------------|------|
| Vs | Supply voltage | ± 18 (36) | V |
| Vi | Input voltage | Vs | |
| Vi | Differential input voltage | ± 15 | V |
| Ιo | Output peak current (internally limited) | 3.5 | А |
| P _{tot} | Power dissipation at $T_{case} = 90^{\circ}C$ | 20 | W |
| T _{stg} , T _j | Stoprage and junction temperature | -40 to 150 | °C |

TYPICAL APPLICATION



PIN CONNECTION (top view)



TEST CIRCUIT



THERMAL DATA

| Symbol | Parameter | Value | Unit |
|------------------------|--------------------------------------|-------|------|
| R _{th j-case} | Thermal resistance junction-case max | 3 | °C/W |

ELECTRICAL CHARACTERISTICS (Refer to the test circuit, V_s = \pm 14V , T_{amb} = 25°C unless otherwise specified) for single Supply refer to fig. 15 Vs = 28V

| Symbol | Parameter | Test conditions | Min. | Тур. | Max. | Unit |
|-----------------|----------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------|---------------|------------|------------|----------|
| Vs | Supply voltage | | ±6 12 | | ± 18 36 | V |
| l _d | Quiescent drain current | | | 40 | 60 | mA |
| l _b | Input bias current | | | 0.2 | 2 | μΑ |
| V _{os} | Input offset voltage | $V_{s} = \pm 18V (Vs = 36V)$ | | ± 2 | ± 20 | mV |
| l _{os} | Input offset current | | | ± 20 | ± 200 | nA |
| Po | Output power | | 12 8 | 14 9 | | \$ \$ |
| | | | | 18 11 | | s s |
| d | Distortion | | | 0.2 | 0.5 | % |
| | | | | 0.1 | 0.5 | % |
| В | Power Bandwidth (-3 dB) | | 10 to 140,000 | | Hz | |
| Ri | Input resistance (pin 1) | | 0.5 | 5 | | MΩ |
| Gv | Voltage gain (open loop) | | | 90 | | dB |
| Gv | Voltage gain (closed loop) | f = 1 kHz | 29.5 | 30 | 30.5 | dB |
| e _N | Input noise voltage | B = 22 Hz to 22 KHz | | 3 | 10 | μV |
| i _N | Input noise current | | | 80 | 200 | pА |
| SVR | Supply voltage rejection | $ \begin{array}{l} R_L = 4\Omega & G_{V} = 30 \; dB \\ R_g = 22 \; k\Omega \\ V_{ripple} = 0.5 \; V_{eff} \\ f_{ripple} = 100 \; Hz \end{array} $ | 40 | 50 | | dB |
| l _d | Drain current | | | 900 500 | | mA mA |

Figure 1. Output power vs. supply voltage



Figure 2. Output power vs. supply voltage



Figure 3. Distortion vs. output power



Figure 4. Distortion vs. output power



Figure 5. Distortion vs. output power



Figure 6. Distortion vs. frequency



Figure 7. Distortion vs. frequency



Figure 8. Frequency response with different values of the rolloff capacitor C8 (see fig. 13)



Figure 9. Quiescent current vs. supply voltage



Figure 10. Supply voltage rejection vs. voltage gain



Figure 11. Power dissipation and efficiency vs. output power

Pto

(w)

16

14

12

10

8

6

4

2

0

Figure 12. Maximum power dissipation vs. supply voltage (sine wave operation)





APPLICATION INFORMATION

Figure 13. Typical amplifier with split power supply



Figure 14. P.C. board and component layout for the circuit of fig. 13 (1 : 1 scale)



APPLICATION INFORMATION (continued)

Figure 15. Typical amplifier with single power supply

Figure 16. P.C. board and component layout for the circuit of fig. 15 (1 : 1 scale)



Figure 17. Bridge amplifier configuration with split power supply ($P_o = 28W$, $V_s = \pm 14V$)



PRACTICAL CONSIDERATIONS

Printed circuit board

The layout shown in Fig. 16 should be adopted by the designers. If different layouts are used, the ground points of input 1 and input 2 must be well decoupled from the ground return of the output in which a high current flows.

Assembly suggestion

No electrical isolation is needed between the

package and the heatsink with single supply voltage configuration.

Application suggestions

The recommended values of the components are those shown on application circuit of fig. 13. Different values can be used. The following table can help the designer.

| Component | Recomm. value | Purpose | Larger than recommended value | Smaller than recommended value | |
|-----------|------------------------------------|-----------------------------------------------------|------------------------------------------------------------------|---------------------------------------|--|
| R1 | 22 kΩ | Closed loop gain setting | Increase of gain | Decrease of gain (*) | |
| R2 | 680 Ω | Closed loop gain setting | Decrease of gain (*) | Increase of gain | |
| R3 | 22 kΩ | Non inverting input biasing | Increase of input impedance | Decrease of input impedance | |
| R4 | 1 Ω | Frequency stability | Danger of osccilat. at high frequencies with induct. loads | | |
| R5 | ≅ 3 R2 | Upper frequency cutoff | Poor high frequencies attenuation | Danger of oscillation | |
| C1 | 1 μF | Input DC decoupling | | Increase of low frequencies cutoff | |
| C2 | 22 μF | Inverting DC decoupling | | Increase of low frequencies cutoff | |
| C3, C4 | 0.1 μF | Supply voltage bypass | | Danger of oscillation | |
| C5, C6 | 100 μF | Supply voltage bypass | | Danger of oscillation | |
| C7 | 0.22 μF | Frequency stability | | Danger of oscillation | |
| C8 | $\cong \frac{1}{2\pi \text{ BR1}}$ | Upper frequency cutoff | Smaller bandwidth | Larger bandwidth | |
| D1, D2 | 1N4001 | To protect the device against output voltage spikes | | | |

(*) Closed loop gain must be higher than 24dB

SINGLE SUPPLY APPLICATION

| Component | Recomm. value | Purpose | Larger than recommended value | Smaller than recommended value | |
|--------------------------------|-------------------------------------|--------------------------------|------------------------------------------------------------------|---------------------------------------|--|
| R1 | 150 kΩ | Closed loop gain setting | Increase of gain | Decrease of gain (*) | |
| R2 | 4.7 kΩ | Closed loop gain setting | Decrease of gain (*) | Increase of gain | |
| R3 | 100 kΩ | Non inverting input biasing | Increase of input impedance | Decrease of input impedance | |
| R4 | 1 Ω | Frequency stability | Danger of osccilat. at high frequencies with induct. loads | | |
| R _A /R _B | 100 kΩ | Non inverting input Biasing | | Power Consumption | |
| C1 | 1 μF | Input DC decoupling | | Increase of low frequencies cutoff | |
| C2 | 22 μF | Inverting DC decoupling | | Increase of low frequencies cutoff | |
| C3 | 0.1 μF | Supply voltage bypass | | Danger of oscillation | |
| C5 | 100 μF | Supply voltage bypass | | Danger of oscillation | |
| C7 | 0.22 μF | Frequency stability | | Danger of oscillation | |
| C8 | $\cong \frac{1}{2\pi \text{ B R1}}$ | Upper frequency cutoff | Smaller bandwidth | Larger bandwidth | |
| D1, D2 | 1N4001 | To protect the device agains | st output voltage spikes | | |

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(*) Closed loop gain must be higher than 24dB

SHORT CIRCUIT PROTECTION

The TDA2030 has an original circuit which limits the current of the output transistors. Fig. 18 shows that the maximum output current is a function of the collector emitter voltage; hence the output transistors work within their safe operating area (Fig. 2). This function can therefore be considered as being

peak power limiting rather than simple current limiting.

It reduces the possibility that the device gets damaged during an accidental short circuit from AC output to ground.





Figure 19. Safe operating area and collector characteristics of the protected power transistor



THERMAL SHUT-DOWN

The presence of a thermal limiting circuit offers the following advantages:

- An overload on the output (even if it is permanent), or an above limit ambient temperature can be easily supported since the T_j cannot be higher than 150°C.
- The heatsink can have a smaller factor of safety compared with that of a conventional circuit. There is no possibility of device damage due to high junction temperature. If for any reason, the

junction temperature increases up to 150°C, the thermal shut-down simply reduces the power dissipation at the current consumption.

The maximum allowable power dissipation depends upon the size of the external heatsink (i.e. its thermal resistance); fig. 22 shows this dissipable power as a function of ambient temperature for different thermal resistance.

Figure 20. Output power and drain current vs. case temperature ($R_L = 4\Omega$)



Figure 21. Output power and drain current vs. case temperature ($R_L = 8\Omega$)







Figure 23. Example of heat-sink



Dimension : suggestion.

The following table shows the length that the heatsink in fig. 23 must have for several values of P_{tot} and R_{th} .

| Ptot (W) | 12 | 8 | 6 |
|----------------------------|-----|-----|-----|
| Length of heatsink (mm) | 60 | 40 | 30 |
| Rth of heatsink (° C/W) | 4.2 | 6.2 | 8.3 |

PENTAWATT PACKAGE MECHANICAL DATA

| DIM | mm | | | inch | | |
|------|------------|-------|-------|-------|-------|-------|
| DIM. | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| Α | | | 4.8 | | | 0.189 |
| С | | | 1.37 | | | 0.054 |
| D | 2.4 | | 2.8 | 0.094 | | 0.110 |
| D1 | 1.2 | | 1.35 | 0.047 | | 0.053 |
| E | 0.35 | | 0.55 | 0.014 | | 0.022 |
| E1 | 0.76 | | 1.19 | 0.030 | | 0.047 |
| F | 0.8 | | 1.05 | 0.031 | | 0.041 |
| F1 | 1 | | 1.4 | 0.039 | | 0.055 |
| G | 3.2 | 3.4 | 3.6 | 0.126 | 0.134 | 0.142 |
| G1 | 6.6 | 6.8 | 7 | 0.260 | 0.268 | 0.276 |
| H2 | | | 10.4 | | | 0.409 |
| H3 | 10.05 | | 10.4 | 0.396 | | 0.409 |
| L | 17.55 | 17.85 | 18.15 | 0.691 | 0.703 | 0.715 |
| L1 | 15.55 | 15.75 | 15.95 | 0.612 | 0.620 | 0.628 |
| L2 | 21.2 | 21.4 | 21.6 | 0.831 | 0.843 | 0.850 |
| L3 | 22.3 | 22.5 | 22.7 | 0.878 | 0.886 | 0.894 |
| L4 | | | 1.29 | | | 0.051 |
| L5 | 2.6 | | 3 | 0.102 | | 0.118 |
| L6 | 15.1 | | 15.8 | 0.594 | | 0.622 |
| L7 | 6 | | 6.6 | 0.236 | | 0.260 |
| L9 | | 0.2 | | | 0.008 | |
| М | 4.23 | 4.5 | 4.75 | 0.167 | 0.177 | 0.187 |
| M1 | 3.75 | 4 | 4.25 | 0.148 | 0.157 | 0.167 |
| V4 | 40° (typ.) | | | | | |
| Dia | 3.65 | | 3.85 | 0.144 | | 0.152 |



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